



SHEET 1 OF 1

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 246065US2S		SERIAL NO. 10/722,514	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Kentaro NAKAJIMA, et al.			
				FILING DATE November 28, 2003		GROUP 2818	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	S					
	AB						
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FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
	AO	S					
	AP						
	AQ						
	AR						
	AS						
	AT						
	AU						
	AV						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
TH	AW	Roy SCHEUERLEIN et al., "A 10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in each Cell", ISSCC Digest of Technical Papers, 2000, Session 7, Paper TA 7.2					
TH	AX	Masashige SATO et al., "Spin-Valve-Like Properties and Annealing Effect in Ferromagnetic Tunnel Junctions", IEEE Transactions on Magnetics, 1997, Vol. 33, No. 5, pp. 3553-3555					
TH	AY	Masashige SATO et al., "Spin-Valve-Like Properties of Ferromagnetic Tunnel Junctions", Jpn. J. Appl. Phys., 1997, Vol. 36, Part 2, pp. 200-201					
TH	AZ	Koichiro INOMATA et al., "Spin-Dependent Tunneling between a Soft Ferromagnetic Layer and Hard Magnetic Nanosize Particles", Jpn. J. Appl. Phys., 1997, Vol. 36, Part 2, pp. 1380-1383				<input type="checkbox"/> Additional References sheet(s) attached	
Examiner TH-STL HIO					Date Considered Feb. 2005		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							